

Massimo Camarda

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

105
papers

997
citations

17
h-index

25
g-index

108
ext. papers

1,089
ext. citations

1.7
avg, IF

3.98
L-index

#	Paper	IF	Citations
105	The Role of Dielectrophoresis for Cancer Diagnosis and Prognosis.. <i>Cancers</i> , 2021 , 14,	6.6	6
104	Ion Implanted Phosphorous for 4H-SiC VDMOSFETs Source Regions: Effect of the Post Implantation Annealing Time. <i>Materials Science Forum</i> , 2020 , 1004, 698-704	0.4	1
103	Surface Morphology of 4H-SiC after Thermal Oxidation. <i>Materials Science Forum</i> , 2019 , 963, 180-183	0.4	1
102	Evidence for carbon clusters present near thermal gate oxides affecting the electronic band structure in SiC-MOSFET. <i>Applied Physics Letters</i> , 2019 , 115, 101601	3.4	10
101	Two-dimensional defect mapping of the SiO ₂ /4H-SiC interface. <i>Physical Review Materials</i> , 2019 , 3,	3.2	9
100	Silicon carbide X-ray beam position monitors for synchrotron applications. <i>Journal of Synchrotron Radiation</i> , 2019 , 26, 28-35	2.4	7
99	Investigation of the Young's Modulus and the Residual Stress of 4H-SiC Circular Membranes on 4H-SiC Substrates. <i>Micromachines</i> , 2019 , 10,	3.3	4
98	SiCILIA-Silicon Carbide Detectors for Intense Luminosity Investigations and Applications. <i>Sensors</i> , 2018 , 18,	3.8	25
97	Electrical properties of extended defects in 4H-SiC investigated by photoinduced current measurements. <i>Applied Physics Express</i> , 2017 , 10, 036601	2.4	6
96	Electronic band structure of the buried SiO ₂ /SiC interface investigated by soft x-ray ARPES. <i>Applied Physics Letters</i> , 2017 , 110, 132101	3.4	5
95	Analysis of 4H-SiC MOS Capacitors on Macro-Stepped Surfaces. <i>Materials Science Forum</i> , 2017 , 897, 107-110	1.0	2
94	Analysis of Thin Thermal Oxides on (0001) SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2017 , 897, 119-124	1.0	1
93	Elution time changes due to anomalous DEP effects in microchannels under uniform and non-uniform electric fields. <i>Sensing and Bio-Sensing Research</i> , 2016 , 8, 59-64	3.3	1
92	Carbon nanotube-based sensing devices for human Arginase-1 detection. <i>Sensing and Bio-Sensing Research</i> , 2016 , 7, 168-173	3.3	20
91	Electrical Properties of Defects in 4H-SiC Investigated by Photo-Induced-Currents Measurements. <i>Materials Science Forum</i> , 2016 , 858, 380-383	0.4	1
90	Analysis of the role of elution buffers on the separation capabilities of dielectrophoretic devices. <i>Sensing and Bio-Sensing Research</i> , 2016 , 7, 162-167	3.3	3
89	4H-SiC(0001) Surface Faceting during Interaction with Liquid Si. <i>Materials Science Forum</i> , 2016 , 858, 163-166	1.0	2

88	Analysis of the role of the particle-wall interaction on the separation efficiencies of field flow fractionation dielectrophoretic devices. <i>Electrophoresis</i> , 2015 , 36, 1396-404	3.6	14
87	Correlations between Crystal Quality and Electrical Properties by Means of Simultaneous Photoluminescence and Photocurrent Analysis. <i>Materials Science Forum</i> , 2015 , 821-823, 257-260	0.4	
86	Interface state density evaluation of high quality hetero-epitaxial 3C-SiC(001) for high-power MOSFET applications. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2015 , 198, 14-19	3.1	14
85	Monte Carlo Study of the early Growth Stages of 3C-SiC on Misoriented $\langle 11-20 \rangle$ and $\langle 1-100 \rangle$; 6H-SiC Substrates: Role of Step-Island Interaction. <i>Materials Science Forum</i> , 2015 , 821-823, 201-204	0.4	1
84	4H-SiC Defects Analysis by Micro Raman Spectroscopy. <i>Materials Science Forum</i> , 2015 , 821-823, 335-338	0.4	1
83	Study of the role of particle-particle dipole interaction in dielectrophoretic devices for biomarkers identification. <i>Lecture Notes in Electrical Engineering</i> , 2015 , 9-12	0.2	3
82	Micro-Raman Characterization of 4H-SiC Stacking Faults. <i>Materials Science Forum</i> , 2014 , 778-780, 378-380	0.4	6
81	Theoretical and experimental study of the role of cell-cell dipole interaction in dielectrophoretic devices: application to polynomial electrodes. <i>BioMedical Engineering OnLine</i> , 2014 , 13, 71	4.1	14
80	Strain Evaluation and Fracture Properties of Hetero-Epitaxial Single Crystal 3C-SiC Squared Membrane. <i>Materials Science Forum</i> , 2014 , 806, 11-14	0.4	
79	Monte Carlo study of the early growth stages of 3C-SiC on misoriented and 6H-SiC substrates: role of step-island interaction. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 1606-1610		
78	Mechanisms of growth and defect properties of epitaxial SiC. <i>Applied Physics Reviews</i> , 2014 , 1, 031301	17.3	56
77	A novel micro-Raman technique to detect and characterize 4H-SiC stacking faults. <i>Journal of Applied Physics</i> , 2014 , 116, 163506	2.5	8
76	4H-SiC Epitaxial Layer Grown on 150 mm Automatic Horizontal Hot Wall Reactor PE106. <i>Materials Science Forum</i> , 2014 , 778-780, 121-124	0.4	7
75	Effects of the Growth Rate on the Quality of 4H Silicon Carbide Films for MOSFET Applications. <i>Materials Science Forum</i> , 2014 , 778-780, 95-98	0.4	1
74	Curvature Evaluation of Si/3C-SiC/Si Hetero-Structure Grown by Chemical Vapor Deposition. <i>Materials Science Forum</i> , 2014 , 778-780, 255-258	0.4	
73	Analysis on 3C-SiC Layer Grown on Pseudomorphic-Si/Si _{1-x} Gex/Si(001) Heterostructures. <i>Materials Science Forum</i> , 2014 , 806, 21-25	0.4	6
72	Monte Carlo Study of the Early Growth Stages of 3C-SiC on Misoriented and 6H-SiC Substrates. <i>Materials Science Forum</i> , 2014 , 778-780, 238-242	0.4	2
71	Fracture property and quantitative strain evaluation of hetero-epitaxial single crystal 3C-SiC membrane. <i>Materials Research Express</i> , 2014 , 1, 015912	1.7	4

70	Evaluation of Mechanical and Optical Properties of Hetero-Epitaxial Single Crystal 3C-SiC Squared-Membrane. <i>Materials Science Forum</i> , 2014 , 778-780, 457-460	0.4	3
69	Monte Carlo Study of the Hetero-Polytypical Growth of Cubic on Hexagonal Silicon Carbide Polytypes. <i>Materials Science Forum</i> , 2013 , 740-742, 295-300	0.4	1
68	Fast Growth Rate Epitaxy by Chloride Precursors. <i>Materials Science Forum</i> , 2013 , 740-742, 167-172	0.4	5
67	Micro-Raman analysis and finite-element modeling of 3 C-SiC microstructures. <i>Journal of Raman Spectroscopy</i> , 2013 , 44, 299-306	2.3	12
66	Post-Growth Process Effect on Hetero-Epitaxial 3C-SiC Wafer Bow and Residual Stress. <i>Materials Science Forum</i> , 2013 , 740-742, 301-305	0.4	1
65	Study of the Effects of Growth Rate, Miscut Direction and Postgrowth Argon Annealing on the Surface Morphology of Homoepitaxially Grown 4H Silicon Carbide Films. <i>Materials Science Forum</i> , 2013 , 740-742, 229-234	0.4	8
64	Stress nature investigation on heteroepitaxial 3CβSiC film on (100) Si substrates. <i>Journal of Materials Research</i> , 2013 , 28, 129-135	2.5	6
63	Correlation between macroscopic and microscopic stress fields: Application to the 3CβSiC/Si heteroepitaxy. <i>Journal of Materials Research</i> , 2013 , 28, 104-112	2.5	4
62	Stress fields analysis in 3CβSiC free-standing microstructures by micro-Raman spectroscopy. <i>Thin Solid Films</i> , 2012 , 522, 20-22	2.2	13
61	Study of microstructure deflections and film/substrate curvature under generalized stress fields and mechanical properties. <i>Thin Solid Films</i> , 2012 , 522, 26-29	2.2	7
60	Monte Carlo study of the hetero-polytypical growth of cubic on hexagonal silicon carbide polytypes. <i>Surface Science</i> , 2012 , 606, 1263-1267	1.8	14
59	Extended Characterization of the Stress Fields in the Heteroepitaxial Growth of 3C-SiC on Silicon for Sensors and Device Applications. <i>Materials Science Forum</i> , 2012 , 717-720, 517-520	0.4	3
58	Micro-Raman Analysis of a Micromachined 3C-SiC Cantilever. <i>Materials Science Forum</i> , 2012 , 717-720, 525-528	0.4	1
57	Mechanical Proprieties and Residual Stress Evaluation on Heteroepitaxial 3C-SiC/Si for MEMS Application. <i>Materials Science Forum</i> , 2012 , 711, 51-54	0.4	4
56	Stress Evaluation on Hetero-Epitaxial 3C-SiC Film on (100) Si Substrates. <i>Materials Science Forum</i> , 2012 , 717-720, 521-524	0.4	3
55	Consideration on the Thermal Expansion of 3C-SiC Epitaxial Layer on Si Substrates. <i>Materials Science Forum</i> , 2012 , 711, 31-34	0.4	1
54	Coupled Monte Carlo-Poisson method for the simulation of particle-particle effects in dielectrophoretic devices. <i>Applied Physics Letters</i> , 2012 , 100, 134104	3.4	19
53	Electron backscattering from stacking faults in SiC by means of ab initio quantum transport calculations. <i>Physical Review B</i> , 2012 , 85,	3.3	27

52	Study of the Impact of Growth and Post-Growth Processes on the Surface Morphology of 4H Silicon Carbide Films. <i>Materials Science Forum</i> , 2012 , 717-720, 149-152	0.4	2
51	Structural Characterization of Heteroepitaxial 3C-SiC. <i>Materials Science Forum</i> , 2012 , 711, 27-30	0.4	5
50	Strain Field Analysis of 3C-SiC Free-Standing Microstructures by Micro-Raman and Theoretical Modelling. <i>Materials Science Forum</i> , 2012 , 711, 55-60	0.4	3
49	Growth and processing of heteroepitaxial 3C-SiC films for electronic devices applications. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1433, 25		2
48	Wafer Cut Effect on Hetero-Epitaxial 3C-SiC Film for MEMS Application. <i>Electrochemical and Solid-State Letters</i> , 2012 , 15, H182		6
47	On the Step Bunching Phenomena Observed on Etched and Homoepitaxially Grown 4H Silicon Carbide. <i>Materials Science Forum</i> , 2011 , 679-680, 358-361	0.4	10
46	Study of the connection between stacking faults evolution and step kinetics in misoriented 4H-SiC epitaxial growths. <i>Surface Science</i> , 2011 , 605, L67-L69	1.8	8
45	Structural and electronic characterization of (2,33) bar-shaped stacking fault in 4H-SiC epitaxial layers. <i>Applied Physics Letters</i> , 2011 , 98, 051915	3.4	16
44	First Principles Investigation on the Modifications of the 4H-SiC Band Structure Due to the (4,4) and (3,5) Stacking Faults. <i>Applied Physics Express</i> , 2011 , 4, 025802	2.4	19
43	Advanced Residual Stress Analysis and FEM Simulation on Heteroepitaxial 3C-SiC for MEMS Application. <i>Journal of Microelectromechanical Systems</i> , 2011 , 20, 745-752	2.5	45
42	High Power Density UV Optical Stress for Quality Evaluation of 4H-SiC Epitaxial Layers. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H457		
41	Raman Stress Characterization of Hetero-Epitaxial 3C-SiC Free Standing Structures. <i>Materials Science Forum</i> , 2011 , 679-680, 141-144	0.4	7
40	Evolution of Extended Defects during Epitaxial Growths: A Monte Carlo Study. <i>Materials Science Forum</i> , 2011 , 679-680, 48-54	0.4	1
39	Publisher's Note: Defect Influence on Heteroepitaxial 3C-SiC Young's Modulus [Electrochem. Solid-State Lett., 14, H161 (2011)]. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, S3		4
38	Complete Determination of the Local Stress Field in Epitaxial Thin Films Using Single Microstructure. <i>Materials Science Forum</i> , 2011 , 679-680, 213-216	0.4	10
37	Advanced Stress Analysis by Micro-Structures Realization on High Quality Hetero-Epitaxial 3C-SiC for MEMS Application. <i>Materials Science Forum</i> , 2011 , 679-680, 133-136	0.4	6
36	Raman Study of Bulk Mobility in 3C-SiC Heteroepitaxy. <i>Materials Science Forum</i> , 2011 , 679-680, 221-224	0.4	4
35	Defect Influence on Heteroepitaxial 3C-SiC Young's Modulus. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H161		33

34	3C-SiC Film Growth on Si Substrates. <i>ECS Transactions</i> , 2011 , 35, 99-116	1	28
33	Advanced Residual Stress Analysis on the Heteroepitaxial Growth of 3C-SiC/Si for MEMS Application. <i>ECS Transactions</i> , 2011 , 35, 123-131	1	1
32	Reduction of the Surface Density of Single Shockley Faults by TCS Growth Process. <i>Materials Science Forum</i> , 2011 , 679-680, 67-70	0.4	9
31	Study of the Evolution of Basal Plane Dislocations during Epitaxial Growth: Role of the Surface Kinetics. <i>Materials Science Forum</i> , 2010 , 645-648, 539-542	0.4	8
30	Raman Characterization of Doped 3C-SiC/Si for Different Silicon Substrates and C/Si Ratios. <i>Materials Science Forum</i> , 2010 , 645-648, 255-258	0.4	17
29	Bow in 6 Inch High-Quality Off-Axis (111) 3C-SiC Films. <i>Materials Science Forum</i> , 2010 , 645-648, 167-170	0.4	2
28	Single Shockley Faults Enlargement during Micro-Photoluminescence Defects Mapping. <i>Materials Science Forum</i> , 2010 , 645-648, 555-558	0.4	7
27	Systematic first principles calculations of the effects of stacking faults defects on the 4H-SiC band structure. <i>Materials Research Society Symposia Proceedings</i> , 2010 , 1246, 1		1
26	Residual Stress Measurement and Simulation of 3C-SiC Single and Poly Crystal Cantilevers. <i>Materials Science Forum</i> , 2010 , 645-648, 865-868	0.4	3
25	Single Shockley faults evolution under UV optical pumping. <i>Materials Research Society Symposia Proceedings</i> , 2010 , 1246, 1		3
24	Systematic First Principles Calculations of the Effects of Stacking Fault Defects on the 4H-SiC Band Structure. <i>Materials Science Forum</i> , 2010 , 645-648, 283-286	0.4	8
23	Evolution of Stacking Faults Defects During Epitaxial Growths: Role of Surface Kinetics.. <i>Materials Research Society Symposia Proceedings</i> , 2010 , 1246, 1		
22	Optical investigation of bulk electron mobility in 3C-SiC films on Si substrates. <i>Applied Physics Letters</i> , 2010 , 97, 142103	3.4	11
21	Low Stress Heteroepitaxial 3C-SiC Films Characterized by Microstructure Fabrication and Finite Elements Analysis. <i>Journal of the Electrochemical Society</i> , 2010 , 157, H438	3.9	20
20	Monte Carlo study of morphological surface instabilities during misoriented epitaxial growth of cubic and hexagonal polytypes 2010 ,		2
19	Multiscale simulation for epitaxial silicon carbide growth by chlorides route. <i>Thin Solid Films</i> , 2010 , 518, S6-S11	2.2	3
18	Extended study of the step-bunching mechanism during the homoepitaxial growth of SiC. <i>Thin Solid Films</i> , 2010 , 518, S159-S161	2.2	20
17	High-quality 6inch (111) 3C-SiC films grown on off-axis (111) Si substrates. <i>Thin Solid Films</i> , 2010 , 518, S165-S169	2.2	55

16	Stacking faults evolution during epitaxial growths: Role of surface the kinetics. <i>Surface Science</i> , 2010 , 604, 939-942	1.8	17
15	Preferential oxidation of stacking faults in epitaxial off-axis (111) 3C-SiC films. <i>Applied Physics Letters</i> , 2009 , 95, 111905	3.4	21
14	Atomistic and Continuum Simulations of the Homo-Epitaxial Growth of SiC. <i>Materials Science Forum</i> , 2009 , 615-617, 73-76	0.4	6
13	Thick Epitaxial Layers Growth by Chlorine Addition. <i>Materials Science Forum</i> , 2009 , 615-617, 55-60	0.4	15
12	Towards Large Area (111)3C-SiC Films Grown on Off-Oriented (111)Si. <i>Materials Science Forum</i> , 2009 , 615-617, 149-152	0.4	4
11	Extended Study of the Step-Bunching Mechanism during the Homoepitaxial Growth of SiC. <i>Materials Science Forum</i> , 2009 , 615-617, 117-120	0.4	2
10	Monte Carlo study of the step flow to island nucleation transition for close packed structures. <i>Surface Science</i> , 2009 , 603, 2226-2229	1.8	15
9	Effect of the miscut direction in (111) 3C-SiC film growth on off-axis (111)Si. <i>Applied Physics Letters</i> , 2009 , 94, 101907	3.4	26
8	Theoretical Monte Carlo Study of the Formation and Evolution of Defects in the Homoepitaxial Growth of SiC. <i>Materials Science Forum</i> , 2008 , 600-603, 135-138	0.4	16
7	Defect formation and evolution in the step-flow growth of silicon carbide: A Monte Carlo study. <i>Journal of Crystal Growth</i> , 2008 , 310, 971-975	1.6	27
6	A kinetic Monte Carlo method on super-lattices for the study of the defect formation in the growth of close packed structures. <i>Journal of Computational Physics</i> , 2007 , 227, 1075-1093	4.1	41
5	Excitable systems as robust event trigger generators in noisy detectors. <i>Physical Review D</i> , 2007 , 76,	4.9	1
4	General interpolation scheme for thermal fluctuations in superconductors. <i>Physical Review B</i> , 2006 , 73,	3.3	17
3	Methods to determine the Hausdorff dimension of vortex loops in the three-dimensional XY model. <i>Physical Review B</i> , 2006 , 74,	3.3	11
2	Search for gravitational wave bursts by wavelet packet decomposition: The detection algorithm. <i>Physical Review D</i> , 2006 , 74,	4.9	4
1	Gaussian Effective Potential and superconductivity. <i>European Physical Journal B</i> , 2003 , 33, 273-277	1.2	22